



GENERAL DESCRIPTION

HC573 is fabricated in the high speed-silicon gate CMOS technology. It has the high noise immunity and low power consumption of standard CMOS integrated circuits. It also offers speeds comparable to low power Schottky devices (LS-TTL).

This 8-bit transparent D-type latch with 3-state outputs is specifically designed for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bi-directional bus drivers, and working registers.

When the latch-enable (LE) input is high, the Q outputs respond to the data (D) inputs. When LE is low, the outputs are latched to retain the data that was set up.

A buffered output-enable input (\overline{OE}) can be used to place the eight outputs in either a normal logic state (H or L logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pull-up components.

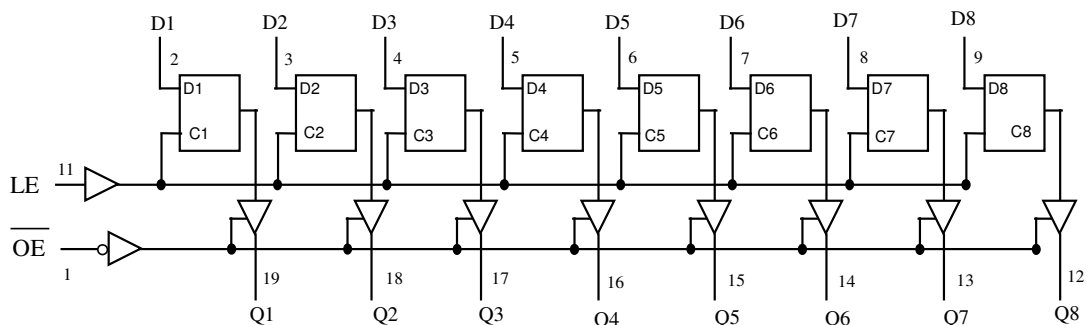
\overline{OE} should be tied to V_{DD} through a pull-up resistor to ensure the high-impedance state during power up or power down; the minimum value of the resistor is determined by the current-sinking capability of the driver.

\overline{OE} does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

FEATURES

- Wide operating supply voltage range: 2-6V
- Output Drive at $V_{DD} = 5V : \pm 6mA$
- Typical propagation delay: 21ns
- Low input current: $< 1\mu A$.
- Low quiescent supply current: 80 μA maximum
- Bus-Structured Pinout
- High-Current 3-state outputs drive bus lines
- Customer-Specific Configuration Control can be supported along with Major-change approval
- Qualified for Automotive Applications

LOGIC DIAGRAM



FUNCTIONAL DESCRIPTION**Truth Table**

Inputs			Output Q
$\overline{\text{OE}}$	LE	D	
L	H	H	H
L	H	L	L
L	LE	X	Q ₀
H	X	X	Z

H = High Level (steady state). L= Low Level (steady state)

X = Irrelevant (any input, including transitions)

Z = high impedance state

Q₀= The level of the output before steady state input conditions were established

ABSOLUTE MAXIMUM RATINGS

Parameter	Value	Unit
DC supply voltage (VDD)	- 0.5 ~ + 7.0	V
DC input or output Voltage (VIN, VOUT)	-0.5 to VDD +0.5	V
DC Current Drain per pin, any output (Iout)	±35	mA
DC Current Drain per pin, VDD or GND (Icc)	±70	mA
Storage Temperature(TSTG)	-65 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the safety of the device cannot be guaranteed.

RECOMMENDED OPERATING CONDITIONS

Parameter		Min.	Normal	Max.	Unit
DC Supply Voltage (VDD)		2.0	5.0	6.0	V
VIH High-level Input Voltage	VDD=2.0V	1.5			V
	VDD=4.5V	3.15			
	VDD=6.0V	4.2			
VIL Low-level Input Voltage	VDD=2.0V			0.5	V
	VDD=4.5V			1.35	
	VDD=6.0V			1.8	
VI Input Voltage		0		VDD	V
VO Output Voltage		0		VDD	V
Operating Temperature (TA)		-40		+125	°C
t _i Input transition time (rise and fall)	VDD=2.0V			1000	ns
	VDD=4.5V			500	
	VDD=6.0V			400	

Note: 2. All unused inputs of the device must be held at VDD or GND to ensure proper device operation.

DC ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Parameter	Test Conditions		VDD	TA = 25°C			TA = -40°C ~125°C		TA = -40°C ~85°C		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
VOH	VI=VIH or VIL	IOH= -20μA	2.0V	1.9	1.998		1.9		1.9	V	
			4.5V	4.4	4.499		4.4		4.4		
			6.0V	5.9	5.999		5.9		5.9		
VOL	VI=VIH or VIL	IOL = 20μA	2.0V		0.002	0.1		0.1		V	
			4.5V		0.001	0.1		0.1			
			6.0V		0.001	0.1		0.1			
VOL	VI=VIH or VIL	IOL = 6mA	4.5V		0.17	0.26		0.4		V	
			6.0V		0.15	0.26		0.4			
VOL	VI=VIH or VIL	IOL = 7.8mA	4.5V		0.17	0.26		0.4		V	
			6.0V		0.15	0.26		0.4			
II	VI=VDD or 0		6.0V		±0.1	±100		±1000		±1000	nA
IOZ	VO =VDD or 0		6.0V		±0.01	±0.5		±10		±5	μA
Icc	VI=VDD or 0	IO =0	6.0V			8		160		80	μA
Ci			2~6V		3	10		10		10	pF

TIMING REQUIREMENTS OVER RECOMMENDED OPERATING TEMPERATURE RANGE (unless otherwise noted)

Parameter	VDD	TA = 25°C		TA = -40°C ~125°C		TA = -40°C ~85°C		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
tw Pulse duration, LE high	2.0V	80		120		100		ns
	4.5V	16		24		20		
	6.0V	14		20		17		
tsu Setup time, data before LE↓	2.0V	50		75		63		ns
	4.5V	10		15		13		
	6.0V	9		13		11		
th Hold time, data after LE↓	2.0V	20		24		24		ns
	4.5V	5		5		5		
	6.0V	5		5		5		

AC ELECTRICAL CHARACTERISTICS (CL = 50pF)

Parameter	From (Input)	To (Output)	VDD	TA =25°C			TA = -40°C ~125°C		TA = -40°C ~85°C		Unit
				Min.	Typ.	Max	Min.	Max.	Min.	Max.	
t _{pd}	D	Q	2.0V		77	175		265		220	ns
			4.5V		26	35		53		44	
			6.0V		23	30		45		38	
	LE	Any Q	2.0V		87	175		265		260	ns
			4.5V		27	35		53		44	
			6.0V		23	30		45		38	
t _{en}	$\overline{\text{OE}}$	Any Q	2.0V		68	150		225		190	ns
			4.5V		24	30		45		38	
			6.0V		21	26		38		32	
t _{dis}	$\overline{\text{OE}}$	Any Q	2.0V		47	150		225		190	ns
			4.5V		23	30		45		38	
			6.0V		21	26		38		32	
t _t		Any Q	2.0V		28	60		90		75	ns
			4.5V		8	12		18		15	
			6.0V		6	10		15		13	

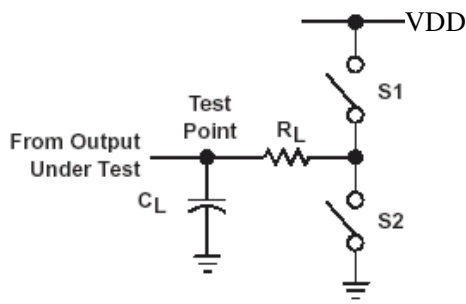
AC ELECTRICAL CHARACTERISTICS (CL = 150pF)

Parameter	From (Input)	To (Output)	VDD	TA =25°C			TA = -40°C ~125°C		TA = -40°C ~85°C		Unit
				Min.	Typ.	Max	Min.	Max.	Min.	Max.	
t _{pd}	D	Q	2.0V		95	200		300		250	ns
			4.5V		33	40		60		50	
			6.0V		21	34		51		43	
	LE	Any Q	2.0V		103	225		335		285	ns
			4.5V		33	45		67		57	
			6.0V		29	38		57		48	
t _{en}	$\overline{\text{OE}}$	Any Q	2.0V		85	200		300		250	ns
			4.5V		29	40		60		50	
			6.0V		26	34		51		43	
t _t		Any Q	2.0V		60	210		315		265	ns
			4.5V		17	42		63		53	
			6.0V		14	36		53		45	

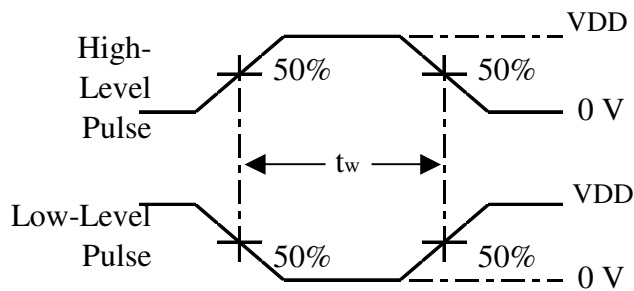
Parameter	Test Conditions	Typ.	Unit
C _{PD} Power Disspation Capitance	TA =25°C , No Load	50	pF

Note 3: C_{PD} determines the no load dynamic power consumption , P_D=C_{PD}· VDD²·f + I_{cc} ·VDD, and the no load dynamic current consumption, I_s = C_{PD}· VDD·f_i + I_{cc}

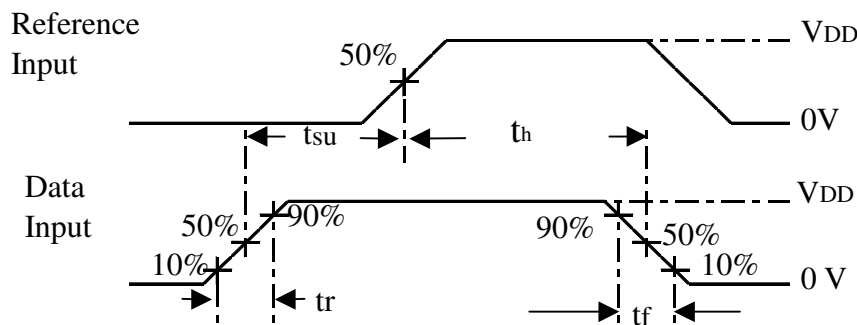
AC TEST CIRCUIT AND AC SWITCHING WAVEFORM



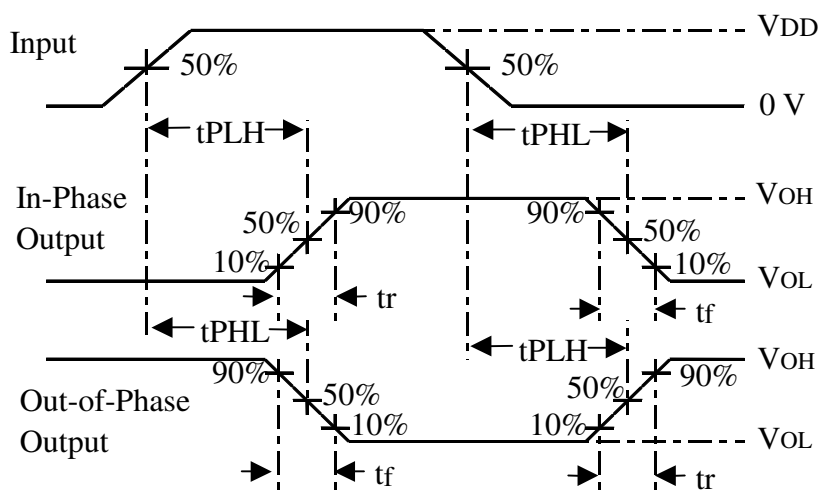
PARAMETER		R_L	C_L	S1	S2
ten	t_{pZH}	1k Ω	50pF or 150pF	Open	Closed
	t_{pZL}			Closed	Open
tdis	t_{pHZ}	1k Ω	50pF	Open	Closed
	t_{pLZ}			Closed	Open
tpd or t_t		---	50pF or 150pF	Open	Open



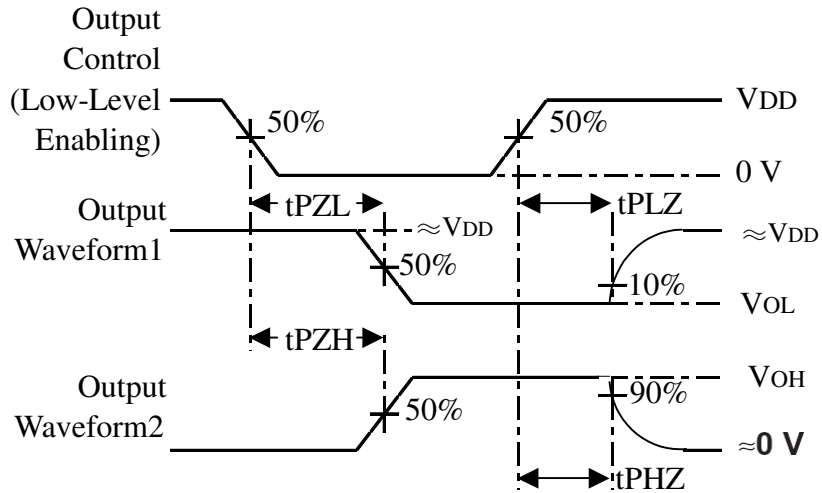
Voltage Waveforms
Pulse Durations



Voltage Waveforms
Setup and Hold and Input Rise and Fall times



Voltage Waveforms
Propagation Delay and Output Transition Times

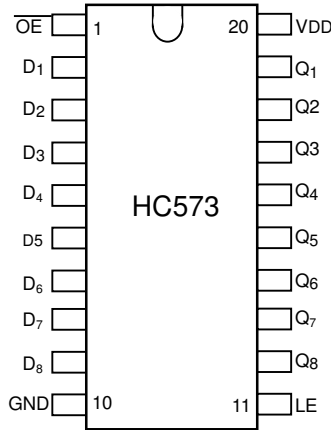


Voltage Waveforms
Enable and disable times for 3-state outputs

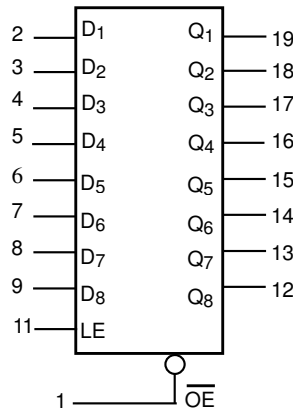
- NOTES 4:**
- 1) C_L includes probe and test-fixture capacitance.
 - 2) Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - 3) Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:
 $PRR \leq 1 \text{ MHz}$, $Z_O = 50\Omega$, $t_r = 6 \text{ ns}$, $t_f = 6 \text{ ns}$.
 - 4) The outputs are measured one at a time, with one input transition per measurement.
 - 5) t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - 6) t_{PZL} and t_{PZH} are the same as t_{en} .
 - 7) t_{PLH} and t_{PHL} are the same as t_{pd} .

PIN DESCRIPTION

PIN NO.	SYMBOL	DESCRIPTION
2 - 9	D1 - D8	Data Inputs
12 - 19	Q8 - Q1	Outputs
10	GND	Ground (0V)
11	<u>LE</u>	Latch-enable input
1	OE	Buffered output-enable
20	VDD	Positive power supply



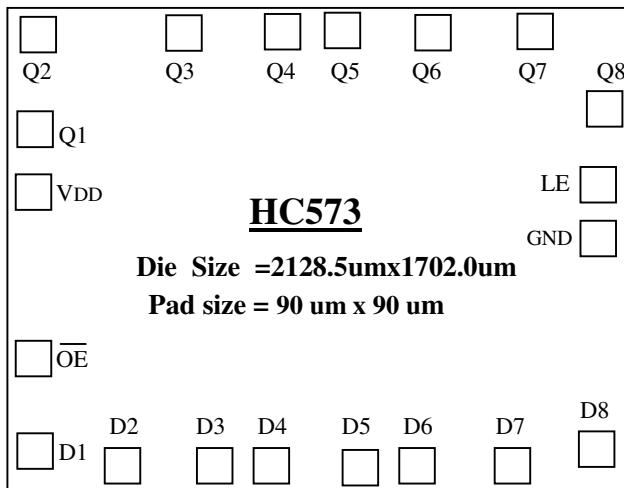
Pin Configuration



Logic Symbol

PAD DIAGRAM

The Coordinate of Each Pad



D1 (-768.3, -555.9)	Q8 (681.3, 313.6)
D2 (-546.5, -594.1)	Q7 (502.1, 510.7)
D3 (-309.0, -594.4)	Q6 (246.0, 510.8)
D4 (-168.5, -594.2)	Q5 (13.6, 510.9)
D5 (60.6, -594.1)	Q4(-134.3, 510.9)
D6 (203.3, -594.0)	Q3 (-389.4, 510.9)
D7 (449.0, -594.1)	Q2 (-760.7, 501.7)
D8 (660.5, -548.1)	Q1 (-766.3, 265.6)
GND (663.5, -16.8)	VDD (-772.7, 106.4)
LE (666.3, 123.7)	OE (-772.7, -323.5)

Note: Substrate should be connected to VDD or left it open.

PAD IDENTIFICATION

